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TCC



MOV



GDT



PIFD

LMV321

Product specification





DESCRIPTION

The LMV321 is single low voltage (2.7V to 5.5V) operational amplifier which has rail-to-rail output swing ca pability. The input common-mode voltage range includes ground. The chip exhibits excellent speed-power ratio, achieving 1MHz of bandwidth and 1V/µs of slew rate with low supply current.

The LMV321 S is built with BiCMOS process. It has bipolar input and output stages for improved noise performance, low input offset and higher output current drive.

The LMV321 is available in the package of SC-70-5, which is approximately half the size of SOT-23-5. The small package saves space on pc boards, and enables the design of small portable electronic devices. It al so allows the designer to place the device closer to the signal source to reduce noise pickup and increase signal integrity.

The LMV321 is also available in standard SOT-23-5 package.

FEATURES (For VCC=5V and VEE=0V, Typical unless Otherwise Noted)

- Guaranteed 2.7V to 5.5V Performance
- No Crossover Distortion
- Gain-Bandwidth Product 1MHz
- Industrial Temperature Range: -40°C to +85°C
- Low Supply Current: 130 μA
- Rail-to-Rail Output Swing under 10kΩ Load:
- VOH up to VCC- 10mV
- VOL near to VEE+65mV
- VCM: -0. 1V to VCC-0.8V

Applications

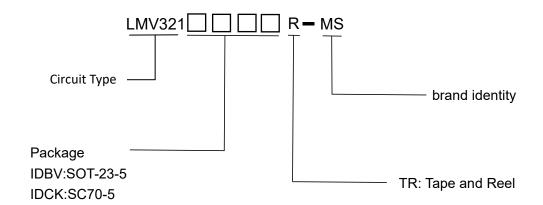
- Active Filters
- Low Power, Low Voltage Applications
- General Purpose Portable Devices
- Cellular Phone, Cordless Phone
- Battery-Powered Systems

Reference News

PACKAGE OUTLINE		PIN CONFIGURATION	Marking		
HEILE FEET		IN+ 1 5 Vcc V _{EE} 2 IN- 3 4 OUTPUT	RC1F	R3F	
SOT-23-5	SC70-5	IDBV/IDCK Package (SC-70-5/SOT-23-5)	SOT-23-5	SC70-5	



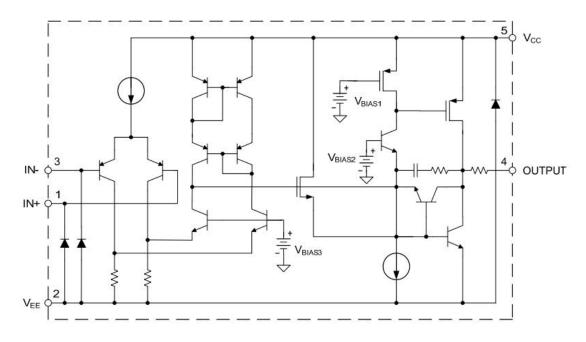
Ordering Information



Dookogo	Temperature	Part Number		Marking ID		Packing	
Package	Range	Lead Free	Green	Lead Free	Green	Туре	
SC-70-5	40 to 95°○		LMV321IDCKR-MS		R3F	Tape & Reel	
SOT-23-5	-40 to 85℃		LMV321IDBVR-MS		RC1F	Tape & Reel	



Functional Block Diagram



Absolute Maximum Ratings (Note 1)

Symbol	Parameter	Rating	Unit
VCC	Power Supply Voltage	6	V
TJ	Operation Junction Temperature	150	°C
TSTG	Storage Temperature Range	-65 to 150	°C
TLEAD	Lead Temperature (Soldering, 10 Seconds)	260	°C
	ESD (Machine Model)	200	V
	ESD (Human Body Model)	2000	V

Note 1: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to "Absolute Maximum Ratings" for extended periods may affect device reliability.

Recommended Operating Conditions

Symbol	Parameter	Min	Max	Unit
VCC	Supply Voltage	2.7	5.5	٧
TA	Ambient Operating Temperature Range	-40	85	°C



Electrical Characteristics

LMV321-2.7V Electrical Characteristic(Asll limits are guaranteed for TA=25°C, VCC=2.7V, VEE=0V, VCM=1.0V, VO=VCC/2 and RL>1MΩ, limits in bold types are guaranteed for TA=-40°C to 85°C, unless otherwise specified. Note 2)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
\				1.7	7	
VIO	Input Offset Voltage				9	mV
IB	Input Bias Current			11	250	
IB	input Blue Guiront				500	nA
lio	Input Offset Current			5	50	5 A
IIO	•				150	nA
VСМ	Input Common Mode Voltage Range	for CMRR≥50dB	-0.1		1.9	V
100	Supply Current	VO=VCC/2, AVCL=1, no load-		80	170	
ICC	сарру санск	VO-VGG/2, AVGE-1, No load			270	μA
CMRR	Common Mode Rejection Ratio	0≤VCM≤ 1.7V	50	65		dB
PSRR	Power Supply Rejection Ratio	2.7V≤VCC≤5V, VO=1V	50	60		dB
ISOURCE	Output Short Circuit Current	VO=0V	5	20		mA
ISINK	Output Griore Grioure Gurrent	VO=2.7V	10	30		mA
VOH	Output Voltage Swing	RL=10kΩ to 1.35V	2.60	2.69		V
VOL	Output Voltage Owing	T(L=10K22 to 1.55 v		60	180	mV
GBWP	Gain Bandwidth Product	CL=200pF		1		MHz
0M	Phase Margin			60		Deg
GM	Gain Margin			10		dB

Note 2: Limits over the full temperature are guaranteed by design, but not tested in production.



Electrical Characteristics (Cont.)

LMV321-5V Electrical Characteristics (All limits are guaranteed for TA=25°C, VCC=5V, VEE=0V, VCM=2.0V, VO=VCC/2 and RL>1M Ω , limits in bold types are guaranteed for TA=-40°C to 85°C, unless otherwise specified. Note 2)

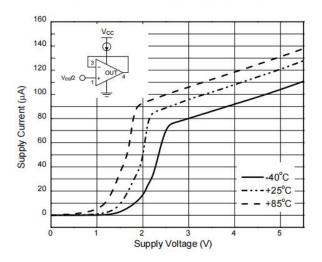
Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
\/\(\c)	l., ., . + Off + \ / - +			1.7	7		
VIO	Input Offset Voltage				9	mV	
ΙΒ	Input Bias Current			11	250	^	
ID					500	nA	
IIO	Input Offset Current			5	50	nA	
110	•				150	117 (
VCM	Input Common Mode Voltage Range	for CMRR≥50dB	-0.1		4.2	V	
ICC	Supply Current	VO=VCC/2, AVCL=1, no load-		130	250		
ICC		VO VOO/2,71VOL 1,110 1000			350	μA	
GV	Large Signal Voltage Gain	RL=2kΩ	84	100		dB	
			80				
CMRR	Common Mode Rejection Ratio	0≤VCM≤4V	50	65		dB	
PSRR	Power Supply Rejection Ratio	2.7V≤VCC≤5V, VO=1V, VCM=1V	50	60		dB	
ISOURCE	Output Short Circuit Current	VO=0V	5	60		mA	
ISINK		VO=5V	10	160		mA	
		RL= $2k\Omega$ to 2.5V	4.7	4.96		V	
VOH			4.6				
V 011			4.9	4.99			
	Output Voltage Swing	TIE TOTAL TO LIGHT	4.8				
		RL=2kΩ to 2.5V		120	300		
VOL		112 2132 to 2.01			400	mV	
		RL=10kΩ to 2.5V		65	180		
		THE TOTAL TO LIGHT			280		
SR	Slew Rate			1		V/µS	
GBWP	Gain Bandwidth Product	CL=200pF		1		MHz	
OM	Phase Margin			60		Deg	
GM	Gain Margin			10		dB	

Note 2: Limits over the full temperature are guaranteed by design, but not tested in production.

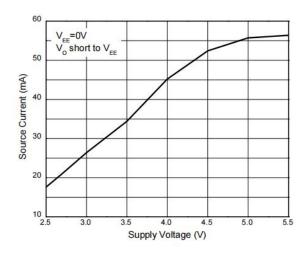


Performance Characteristics

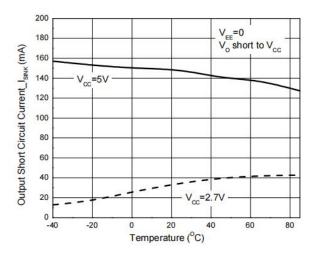
Supply Current vs. Supply Voltage



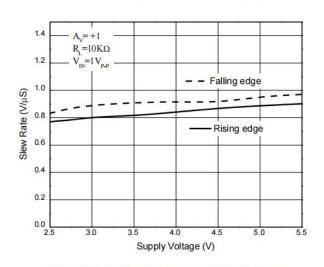
Output Source Current vs. Supply Voltage



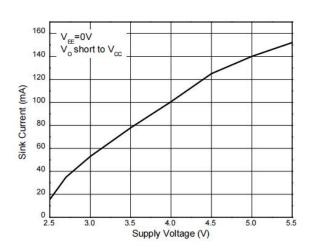
Short Circuit Current_Isink vs. Temperature



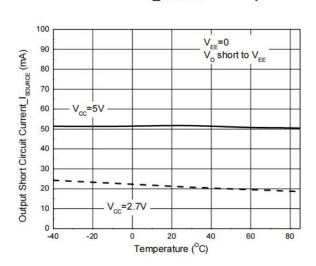
Slew Rate vs. Supply Voltage



Output Sink Current vs. Supply Voltage



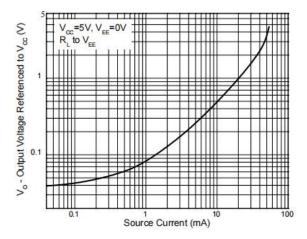
Short Circuit Current_Isource vs. Temperature



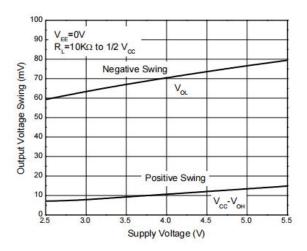


Performance Characteristics (Cont.)

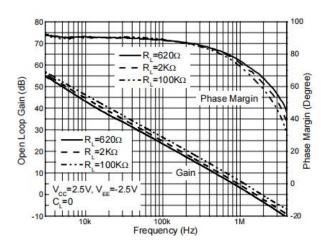
Output Voltage vs. Source Current



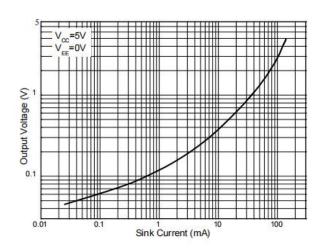
Output Voltage Swing vs. Supply Voltage



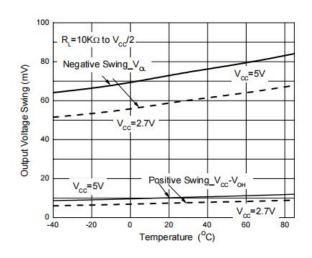
Gain and Phase vs. Frequency and Resistive Load



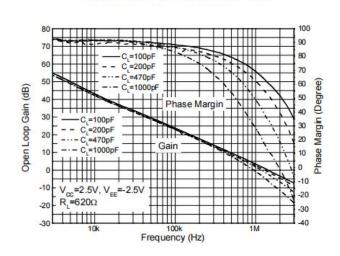
Output Voltage vs. Sink Current



Output Voltage Swing vs. Temperature



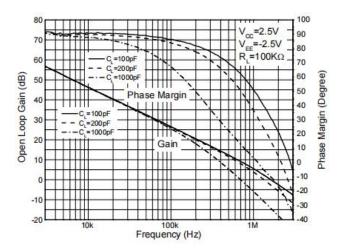
Gain and Phase vs. Frequency and Capacitive Load



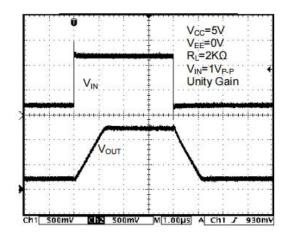


Performance Characteristics (Cont.)

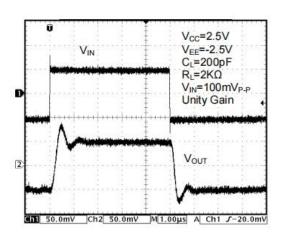
Gain and Phase vs. Frequency and Capacitive Load



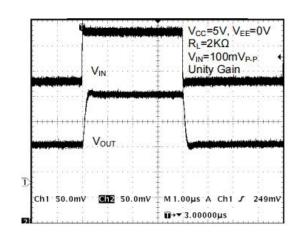
Non-Inverting Input Large Signal Pulse Response



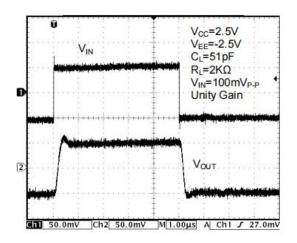
Output with Excessive Capacitive Load



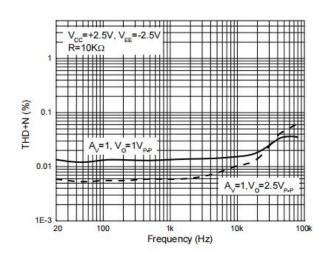
Non-Inverting Input Small Signal Pulse Response



Output with Excessive Capacitive Load



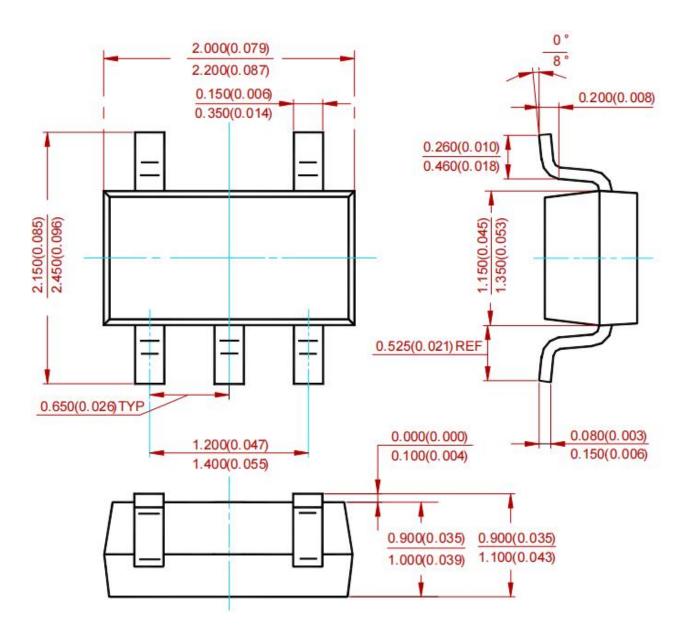
THD+N vs. Frequency





Package Outline Dimensions (All dimensions in mm(inch).)

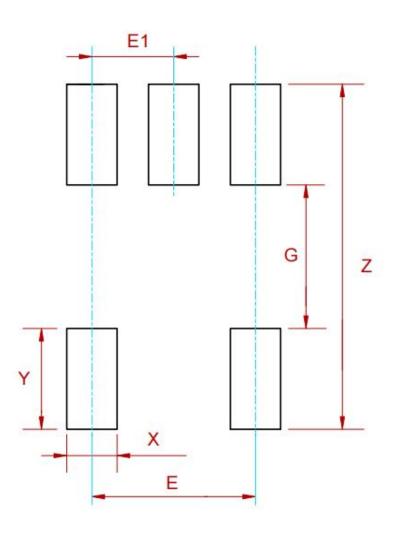
SC-70-5





Suggested Pad Layout

SC-70-5

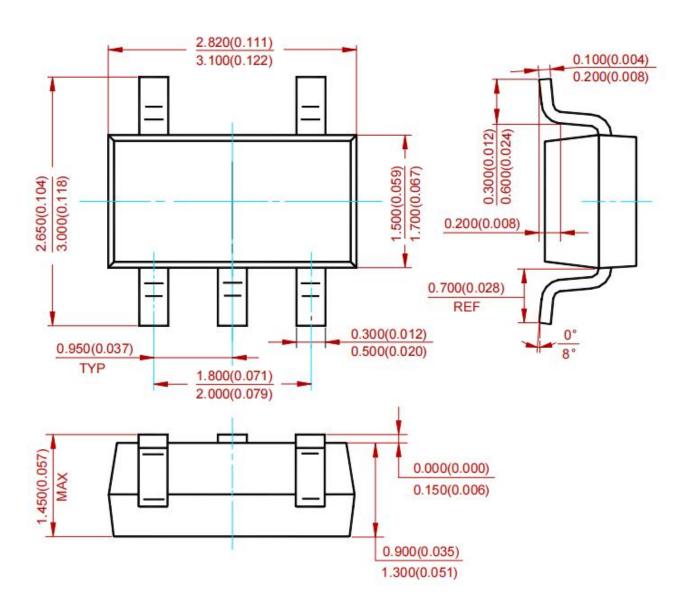


Dimensions	Z	G	X	Y	E	E1
	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)
Value	2.740/0. 108	1. 140/0.045	0.400/0.016	0.800/0.031	1.300/0.051	0.650/0.026



Package Outline Dimensions (All dimensions in mm(inch).)

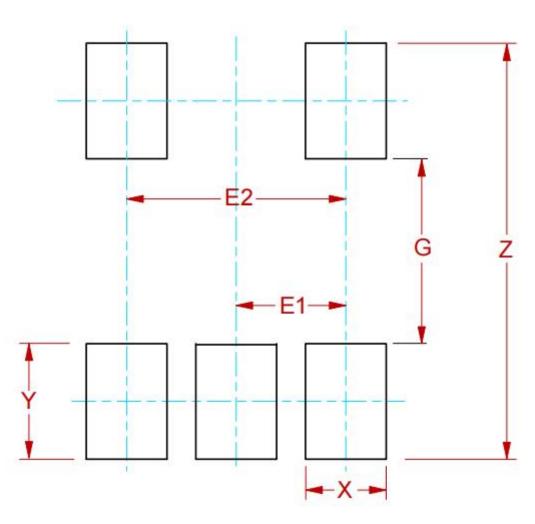
SOT-23-5





Suggested Pad Layout

SOT-23-5



Dimensions	Z	G	X	Y	E1	E2
	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)	(mm)/(inch)
Value	3.600/0. 142	1.600/0.063	0.700/0.028	1.000/0.039	0.950/0.037	1.900/0.075



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